Transistors

2SA2079

Silicon PNP epitaxial planar type

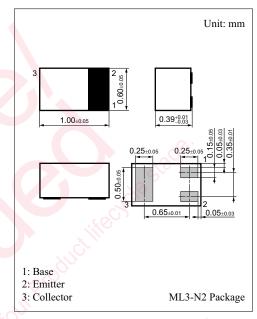
For general amplification Complementary to 2SC5848

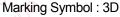
Features

- \bullet High forward current transfer ratio h_{FE}
- Suitable for high-density mounting and douwsizing of the equipment for ultraminiature leadless package Package: 0.6 mm × 1.0 mm (hight 0.39 mm)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -45 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | -45 | V | |
| Emitter-base voltage (Collector open) | V _{EBO} | -7 | v | |
| Collector current | I _C | -100 | mA | |
| Peak collector current | I _{CP} | -200 | mA | |
| Collector power dissipation | P _C | 100 | mW | |
| Junction temperature | Tj | 125 | °C | |
| Storage temperature | T _{stg} | -55 to +125 | °C | |





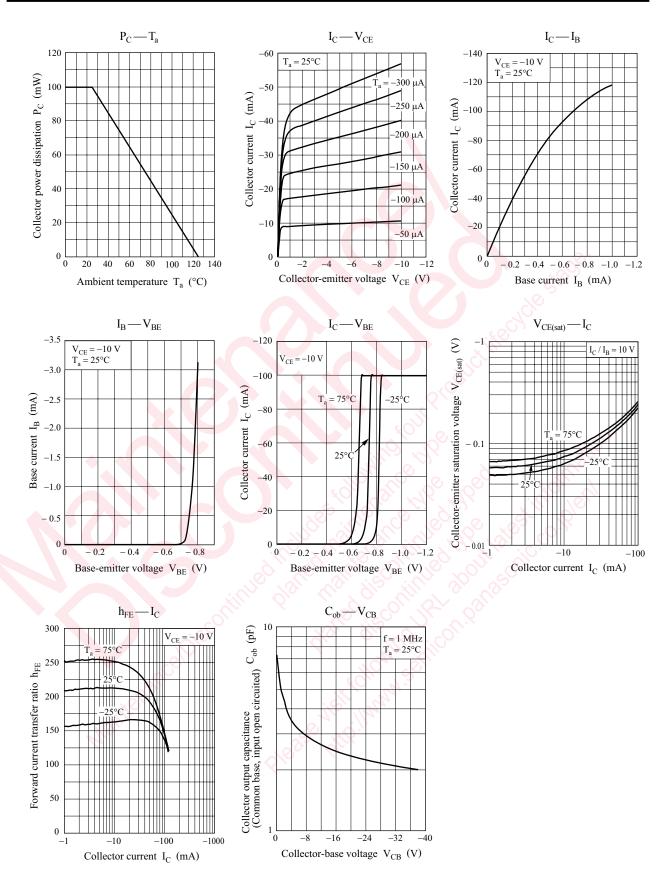
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|---|-----|-------|-------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$ | -45 | 5 | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$ | -45 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_{\rm E} = -10 \ \mu {\rm A}, I_{\rm C} = 0$ | -7 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = -20 V, I_E = 0$ | | | - 0.1 | μΑ |
| Collector-emitter cut-off current (Base open) | I _{CEO} | $V_{CE} = -10 \text{ V}, I_B = 0$ | | | -100 | μΑ |
| Forward current transfer ratio | h _{FE} | $V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$ | 180 | | 390 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$ | | - 0.2 | - 0.5 | V |
| Transition frequency | f _T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 2.2 | | pF |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2SA2079

Panasonic



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